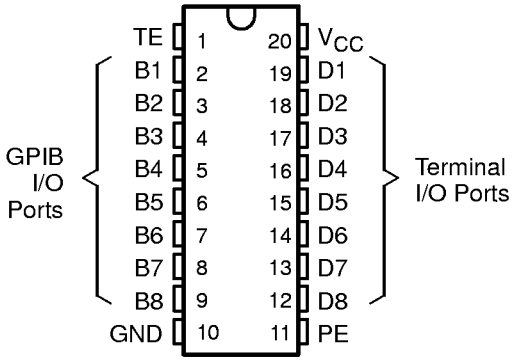
SN75ALS163
OCTAL GENERAL-PURPOSE INTERFACE BUS TRANSCEIVER

SLLS021E – JUNE 1986 – REVISED MAY 1998

- 8-Channel Bidirectional Transceiver
- High-Speed Advanced Low-Power Schottky Circuitry
- Low Power Dissipation . . . 46 mW Max per Channel
- Fast Propagation Times . . . 20 ns Max
- High-Impedance pnp Inputs
- Receiver Hysteresis . . . 650 mV Typ
- Open-Collector Driver Output Option
- No Loading of Bus When Device Is Powered Down (V_{CC} = 0)
- Power-Up/Power-Down Protection (Glitch Free)

DW PACKAGE
(TOP VIEW)



NOT RECOMMENDED FOR NEW DESIGNS

description

The SN75ALS163 octal general-purpose interface bus transceiver is a monolithic, high-speed, advanced low-power Schottky device. It is designed for two-way data communications over single-ended transmission lines. The transceiver features driver outputs that can be operated in either the open-collector or 3-state mode. If talk enable (TE) is high, these outputs have the characteristics of open-collector outputs when pullup enable (PE) is low and of 3-state outputs when PE is high. Taking TE low places the outputs in the high-impedance state. The driver outputs are designed to handle loads of up to 48 mA of sink current. Each receiver features pnp transistor inputs for high input impedance and 400 mV minimum of hysteresis for increased noise immunity.

Output glitches during power up and power down are eliminated by an internal circuit that disables both the bus and receiver outputs. The outputs do not load the bus when V_{CC} = 0.

The SN75ALS163 is characterized for operation from 0°C to 70°C.

Function Tables

EACH DRIVER

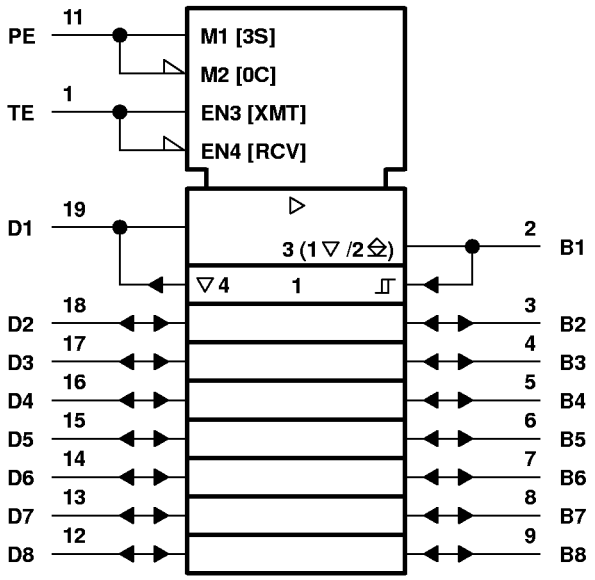
INPUTS			OUTPUT
D	TE	PE	B
H	H	H	H
L	H	X	L
H	X	L	Z
X	L	X	Z

EACH RECEIVER

INPUTS			OUTPUT
B	TE	PE	D
L	L	X	L
H	L	X	H
X	H	X	Z

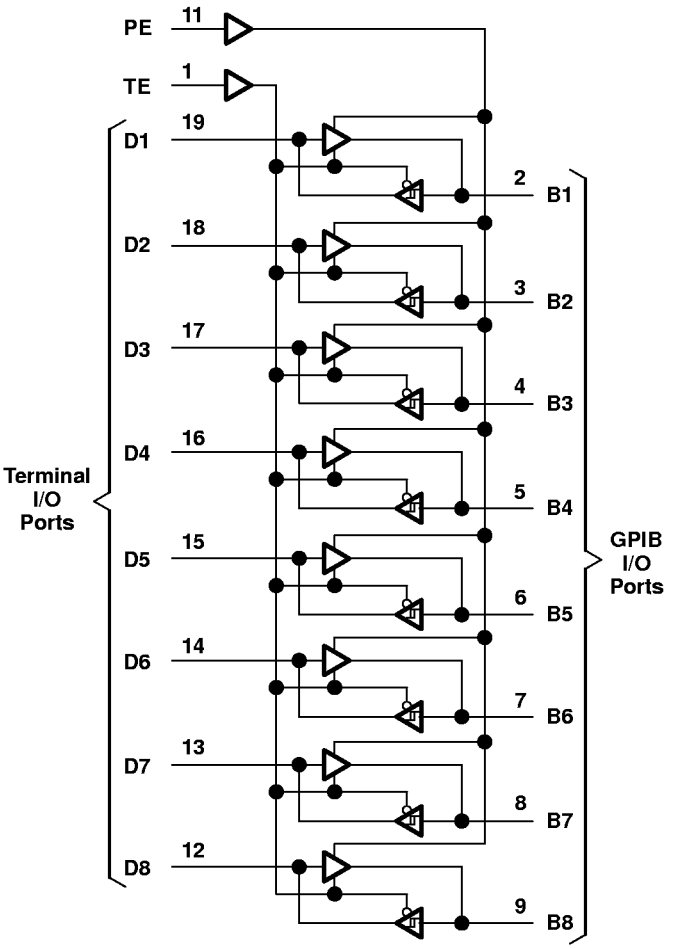
H = high level, L = low level,
X = irrelevant, Z = high-impedance state

logic symbol†

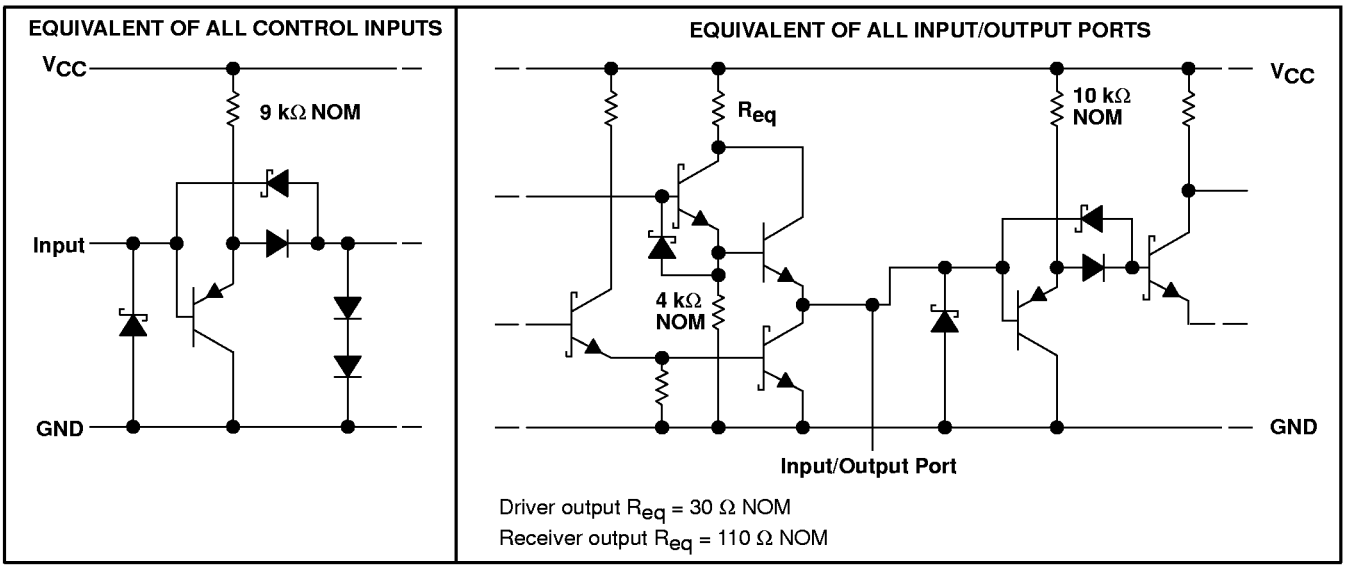


† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.
▽ Designates 3-state outputs
◈ Designates open-collector outputs

logic diagram (positive logic)



schematics of inputs and outputs



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage, V_{CC} (see Note 1) . . . . . 7 V
Input voltage, V_I . . . . . 5.5 V
Low-level driver output current . . . . . 100 mA
Package thermal impedance, θ_{JA} (see Note 2) . . . . . 97°C/W
Storage temperature range, T_{stg} . . . . . – 65°C to 150°C
Lead temperature 1,6 mm (1/16 inch) from the case for 10 seconds . . . . . 260°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. All voltage values are with respect to network ground terminal.
2. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions

		MIN	NOM	MAX	UNIT
Supply voltage, V_{CC}		4.75	5	5.25	V
High-level input voltage, V_{IH}		2			V
Low-level input voltage, V_{IL}				0.8	V
High-level output current, I_{OH}	Bus ports with pullups active			– 5.2	mA
	Terminal ports			– 800	µA
Low-level output current, I_{OL}	Bus ports			48	mA
	Terminal ports			16	
Operating free-air temperature, T_A		0		70	°C

electrical characteristics over recommended supply-voltage and operating free-air temperature ranges (unless otherwise noted)

PARAMETER			TEST CONDITIONS		MIN	TYP†	MAX	UNIT
V_{IK}	Input clamp voltage		I_I = –18 mA			– 0.8	–1.5	V
V_{hys}	Hysteresis ($V_{T+} - V_{T-}$)	Bus			0.4	0.65		V
V_{OH}	High-level output voltage	Terminal	I_{OH} = – 800 μA,	TE at 0.8 V	2.7	3.5		V
		Bus	I_{OH} = – 5.2 mA,	PE and TE at 2 V	2.5	3.3		
V_{OL}	Low-level output voltage	Terminal	I_{OL} = 16 mA,	TE at 0.8 V		0.3	0.5	V
		Bus	I_{OL} = 48 mA,	TE at 2 V		0.35	0.5	
I_{OH}	High-level output current (open-collector mode)	Bus	V_O = 5.5 V,	PE at 0.8 V, D and TE at 2 V			100	μA
I_{OZ}	Off-state output current (3-state mode)	Bus	PE at 2 V, TE at 0.8 V	V_O = 2.7 V			20	μA
				V_O = 0.5 V			–100	
I_I	Input current at maximum input voltage	Terminal	V_I = 5.5 V			0.2	100	μA
I_{IH}	High-level input current	Terminal, PE, or TE	V_I = 2.7 V			0.1	20	μA
I_{IL}	Low-level input current		V_I = 0.5 V			–10	–100	μA
I_{OS}	Short-circuit output current	Terminal			– 15	– 35	– 75	mA
		Bus			– 25	– 50	–125	
I_{CC}	Supply current		No load	Terminal outputs low and enabled		42	65	mA
				Bus outputs low and enabled		52	80	
$C_{I/O(bus)}$	Bus-port capacitance		V_{CC} = 0 to 5 V,	$V_{I/O}$ = 0 to 2 V, f = 1 MHz		30		pF

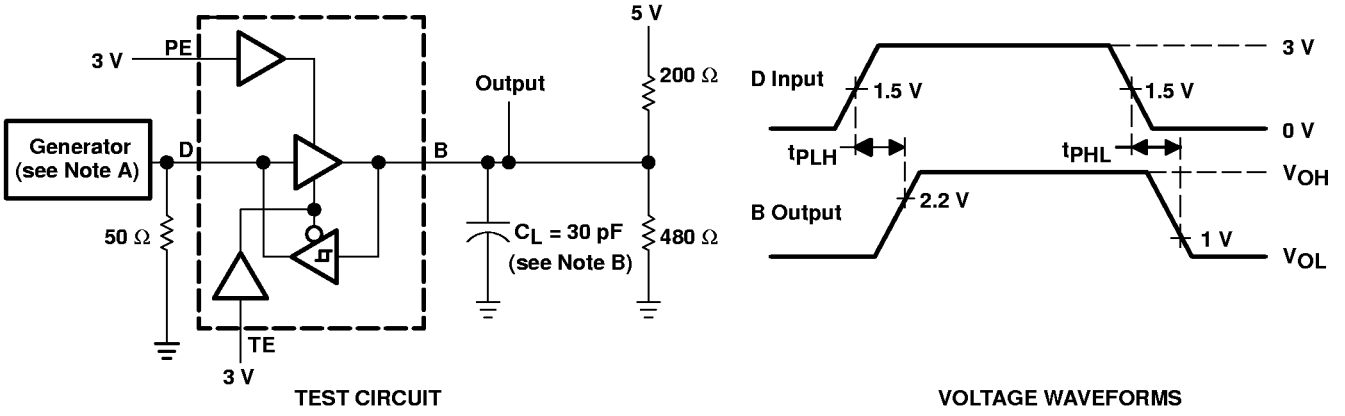
† All typical values are at V_{CC} = 5 V, T_A = 25°C.

switching characteristics over recommended operating free-air temperature range (unless otherwise noted), V_{CC} = 5 V

PARAMETER		FROM (INPUT)	TO (OUTPUT)	TEST CONDITIONS	MIN	TYP†	MAX	UNIT
t_{PLH}	Propagation delay time, low-to-high-level output	Terminal	Bus	C_L = 30 pF, See Figure 1		7	20	ns
t_{PHL}	Propagation delay time, high-to-low-level output					8	20	
t_{PLH}	Propagation delay time, low-to-high-level output	Bus	Terminal	C_L = 30 pF, See Figure 2		7	14	ns
t_{PHL}	Propagation delay time, high-to-low-level output					9	14	
t_{PZH}	Output enable time to high level	TE	Bus	C_L = 15 pF, See Figure 3		19	30	ns
t_{PHZ}	Output disable time from high level					5	12	
t_{PZL}	Output enable time to low level					16	35	
t_{PLZ}	Output disable time from low level					9	20	
t_{PZH}	Output enable time to high level	TE	Terminal	C_L = 15 pF, See Figure 4		13	30	ns
t_{PHZ}	Output disable time from high level					12	20	
t_{PZL}	Output enable time to low level					12	20	
t_{PLZ}	Output disable time from low level					11	20	
t_{en}	Output pull-up enable time	PE	Bus	C_L = 15 pF, See Figure 5		11	22	ns
t_{dis}	Output pull-up disable time					6	12	

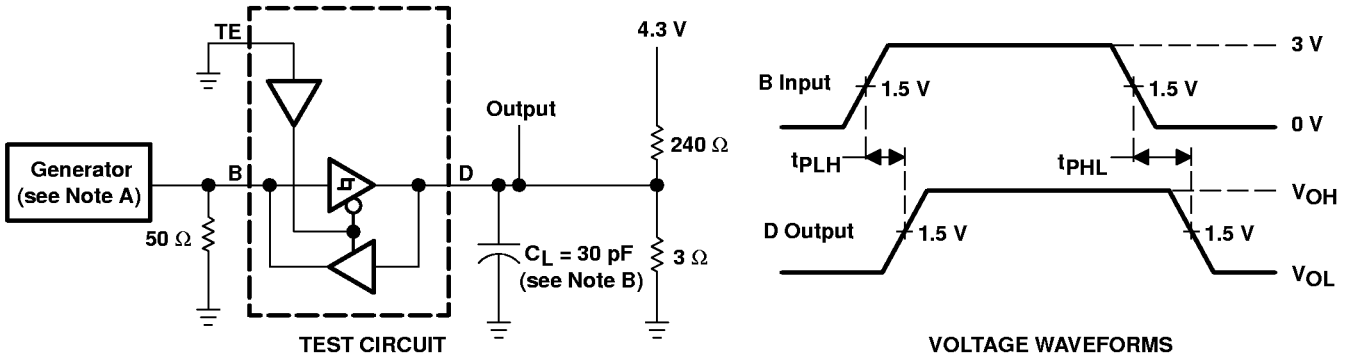
† All typical values are at V_{CC} = 5 V, T_A = 25°C.

PARAMETER MEASUREMENT INFORMATION



NOTES: A. The input pulse is supplied by a generator having the following characteristics: PRR ≤ 1 MHz, 50% duty cycle, t_r ≤ 6 ns, t_f ≤ 6 ns, Z_O = 50 Ω.
B. C_L includes probe and jig capacitance.

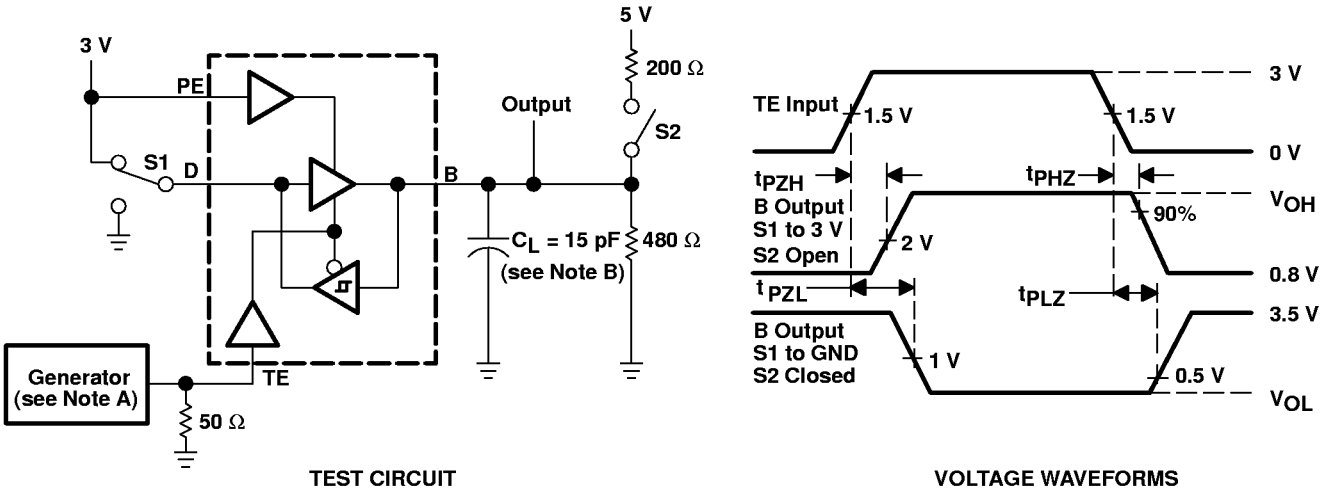
Figure 1. Terminal-to-Bus Test Circuit and Voltage Waveforms



NOTES: A. The input pulse is supplied by a generator having the following characteristics: PRR ≤ 1 MHz, 50% duty cycle, t_r ≤ 6 ns, t_f ≤ 6 ns, Z_O = 50 Ω.
B. C_L includes probe and jig capacitance.

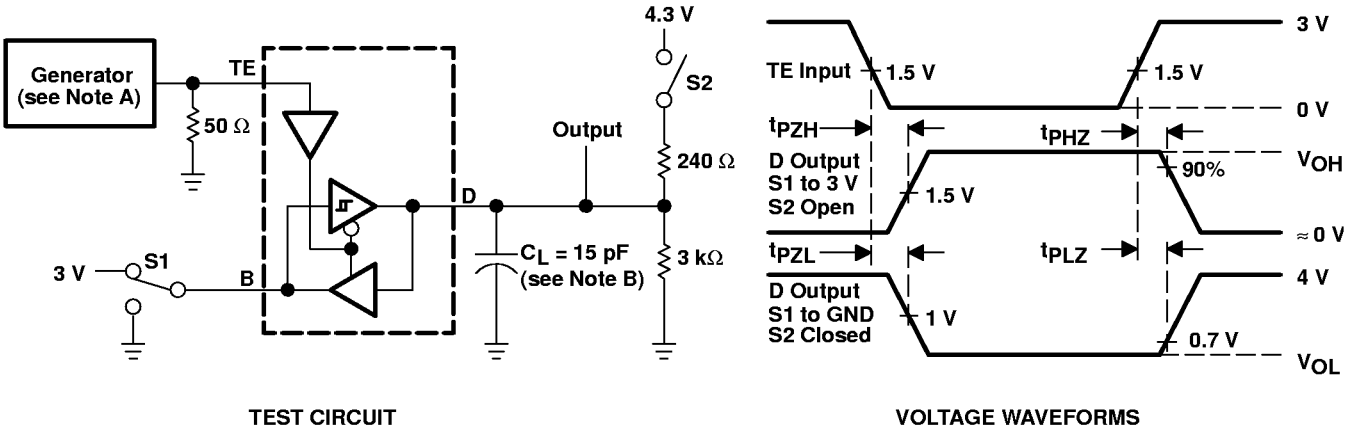
Figure 2. Bus-to-Terminal Test Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION



NOTES: A. The input pulse is supplied by a generator having the following characteristics: PRR ≤ 1 MHz, 50% duty cycle, t_r ≤ 6 ns, t_f ≤ 6 ns, Z_O = 50 Ω.
B. C_L includes probe and jig capacitance.

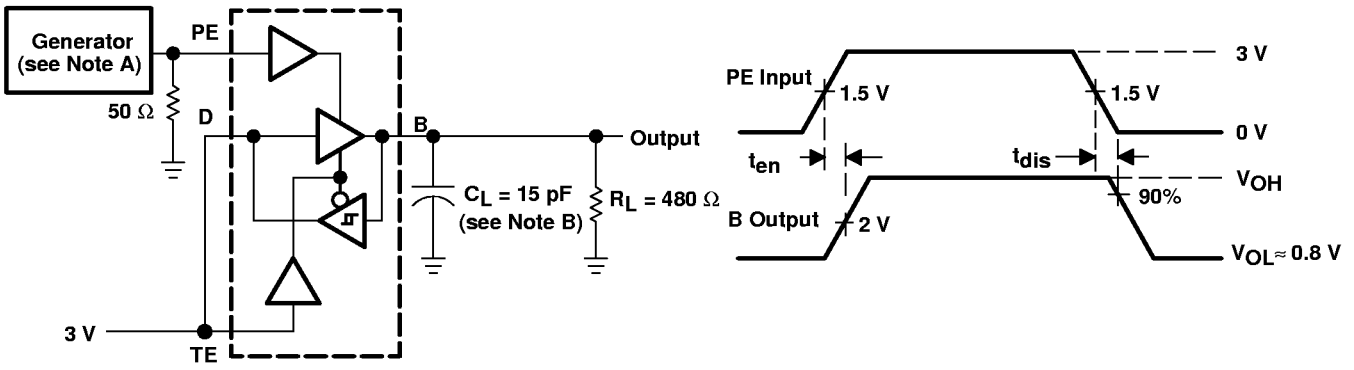
Figure 3. TE-to-Bus Test Circuit and Voltage Waveforms



NOTES: A. The input pulse is supplied by a generator having the following characteristics: PRR ≤ 1 MHz, 50% duty cycle, t_r ≤ 6 ns, t_f ≤ 6 ns, Z_O = 50 Ω.
B. C_L includes probe and jig capacitance.

Figure 4. TE-to-Terminal Test Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION



TEST CIRCUIT

VOLTAGE WAVEFORMS

NOTES: A. The input pulse is supplied by a generator having the following characteristics: PRR ≤ 1 MHz, 50% duty cycle, t_r ≤ 6 ns, t_f ≤ 6 ns, Z_O = 50 Ω.
B. C_L includes probe and jig capacitance.

Figure 5. PE-to-Bus Test Circuit and Voltage Waveforms

TYPICAL CHARACTERISTICS

TERMINAL HIGH-LEVEL OUTPUT VOLTAGE vs HIGH-LEVEL OUTPUT CURRENT

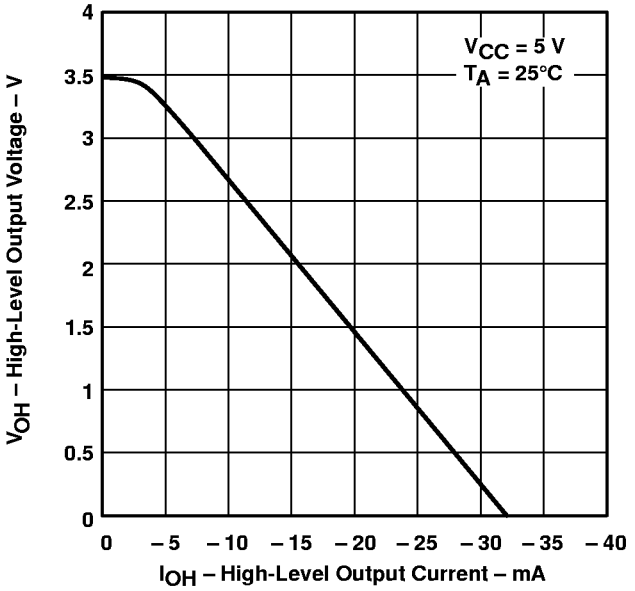


Figure 6

TERMINAL LOW-LEVEL OUTPUT VOLTAGE vs LOW-LEVEL OUTPUT CURRENT

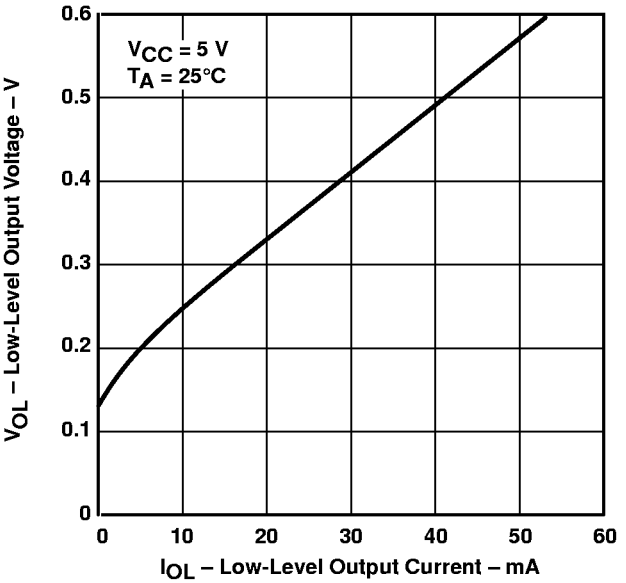


Figure 7

TERMINAL OUTPUT VOLTAGE vs BUS INPUT VOLTAGE

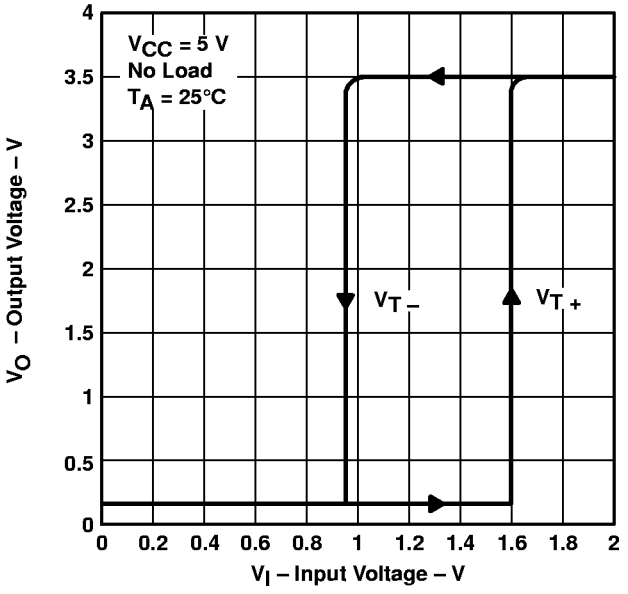


Figure 8

TYPICAL CHARACTERISTICS

BUS HIGH-LEVEL OUTPUT VOLTAGE vs BUS HIGH-LEVEL OUTPUT CURRENT

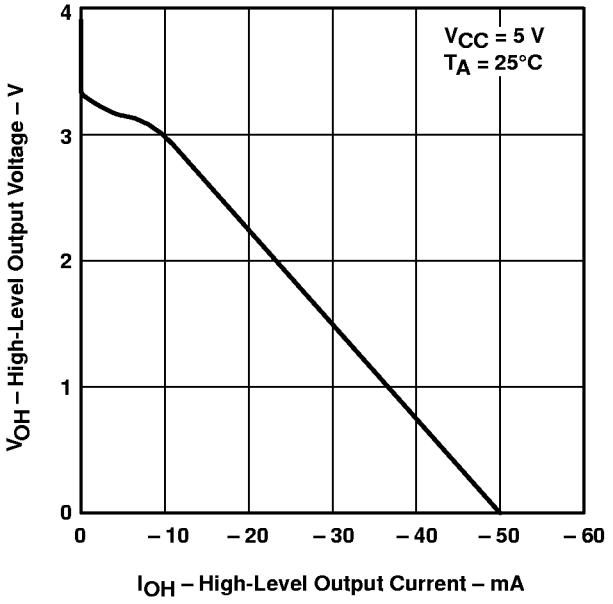


Figure 9

BUS LOW-LEVEL OUTPUT VOLTAGE vs BUS LOW-LEVEL OUTPUT CURRENT

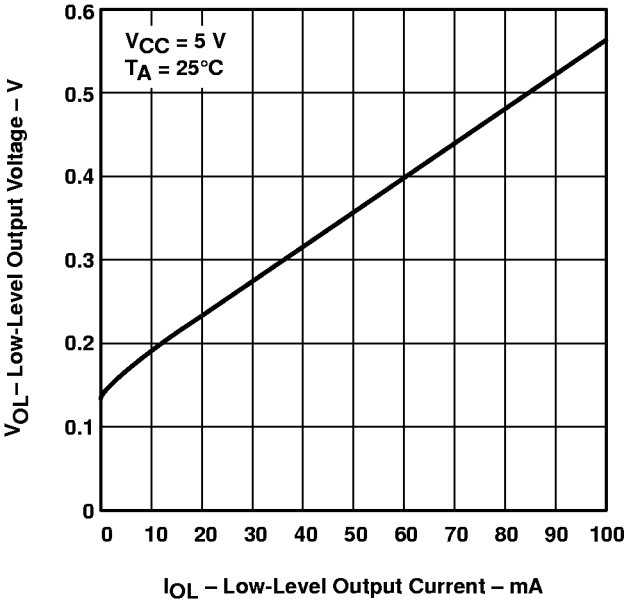


Figure 10

BUS OUTPUT VOLTAGE vs TERMINAL INPUT VOLTAGE

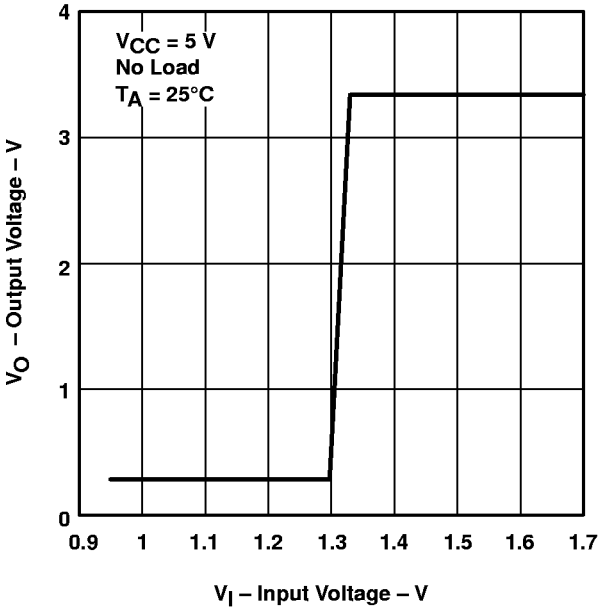


Figure 11

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